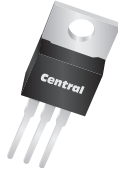


CS220-8B
 CS220-8D
 CS220-8M
 CS220-8N

**SILICON CONTROLLED RECTIFIERS
 8.0 AMP, 200 THRU 800 VOLT**



TO-220 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CS220-8B series types are epoxy molded SCRs designed for sensing circuit and control system applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	CS220				UNITS
		-8B	-8D	-8M	-8N	
Peak Repetitive Off-State Voltage	V_{DRM}, V_{RRM}	200	400	600	800	V
RMS On-State Current ($T_C=90^\circ\text{C}$)	$I_T(\text{RMS})$		8.0			A
Peak One Cycle Surge Current, $t=10\text{ms}$	I_{TSM}		60			A
I^2t Value for Fusing, $t=10\text{ms}$	I^2t		18			A^2s
Peak Gate Power Dissipation, $t_p=10\mu\text{s}$	P_{GM}		40			W
Average Gate Power Dissipation	$P_{G(AV)}$		1.0			W
Peak Forward Gate Current, $t_p=10\mu\text{s}$	I_{FGM}		4.0			A
Peak Forward Gate Voltage, $t_p=10\mu\text{s}$	V_{FGM}		16			V
Peak Reverse Gate Voltage, $t_p=10\mu\text{s}$	V_{RGM}		5.0			V
Critical Rate of Rise of On-State Current	di/dt		50			$\text{A}/\mu\text{s}$
Operating Junction Temperature	T_J		-40 to +125			$^\circ\text{C}$
Storage Temperature	T_{stg}		-40 to +150			$^\circ\text{C}$
Thermal Resistance	θ_{JA}		60			$^\circ\text{C}/\text{W}$
Thermal Resistance	θ_{JC}		2.5			$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

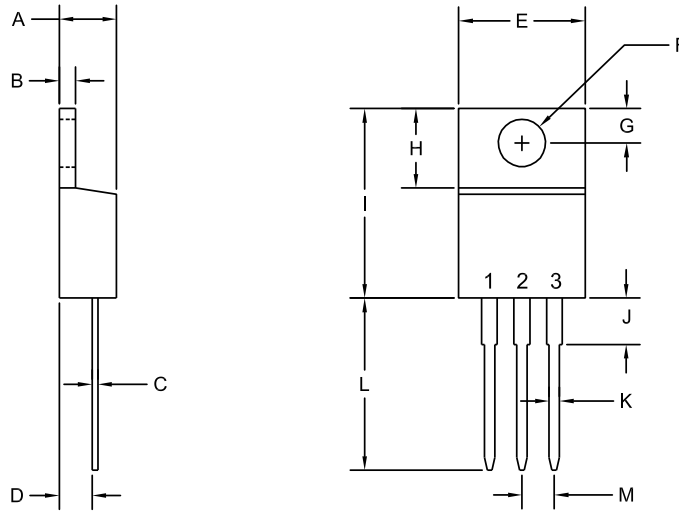
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{DRM}, I_{RRM}	Rated V_{DRM}, V_{RRM}			10	μA
I_{DRM}, I_{RRM}	Rated $V_{DRM}, V_{RRM}, T_C=125^\circ\text{C}$			2.0	mA
I_{GT}	$V_D=12\text{V}, R_L=10\Omega$		3.0	15	mA
I_H	$I_T=100\text{mA}$		7.3	20	mA
V_{GT}	$V_D=12\text{V}, R_L=10\Omega$		0.9	1.5	V
V_{TM}	$I_{TM}=16\text{A}, t_p=380\mu\text{s}$		1.3	1.8	V
dv/dt	$V_D=\frac{2}{3}\text{Rated } V_{DRM}, T_C=125^\circ\text{C}$	200			$\text{V}/\mu\text{s}$

CS220-8B
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SILICON CONTROLLED RECTIFIERS
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TO-220 CASE - MECHANICAL OUTLINE



R2

LEAD CODE:

- 1) Cathode
 - 2) Anode
 - 3) Gate
- Tab is common to pin 2

MARKING:

FULL PART NUMBER

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.170	0.190	4.31	4.82
B	0.045	0.055	1.15	1.39
C	0.013	0.026	0.33	0.65
D	0.083	0.107	2.10	2.72
E	0.394	0.417	10.01	10.60
F (DIA)	0.140	0.157	3.55	4.00
G	0.100	0.118	2.54	3.00
H	0.230	0.270	5.85	6.85
I	0.560	0.625	14.23	15.87
J	-	0.250	-	6.35
K	0.025	0.038	0.64	0.96
L	0.500	0.579	12.70	14.70
M	0.090	0.110	2.29	2.79

TO-220 (REV: R2)

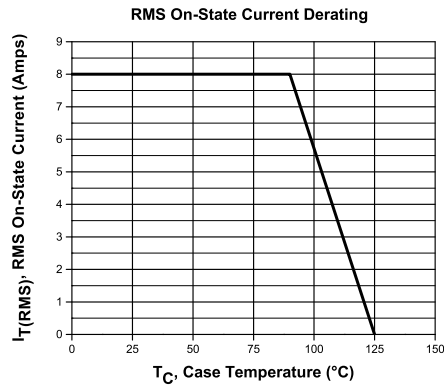
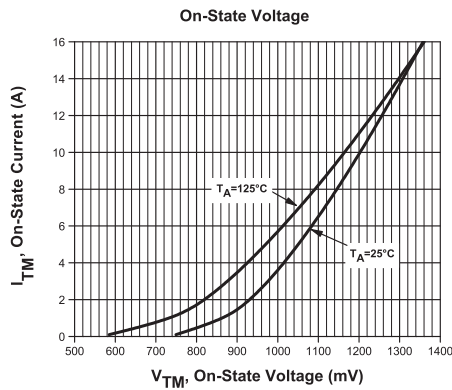
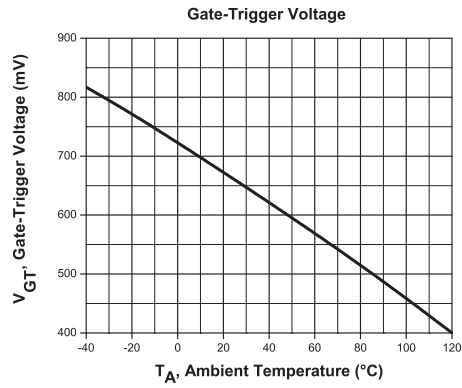
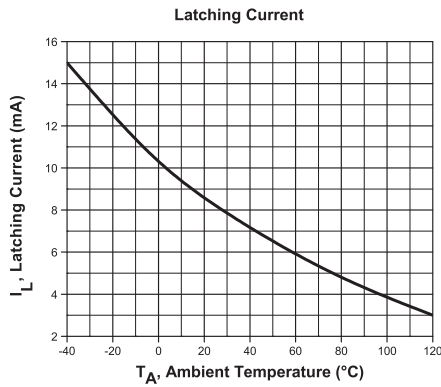
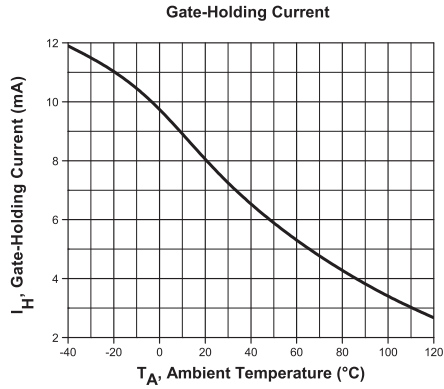
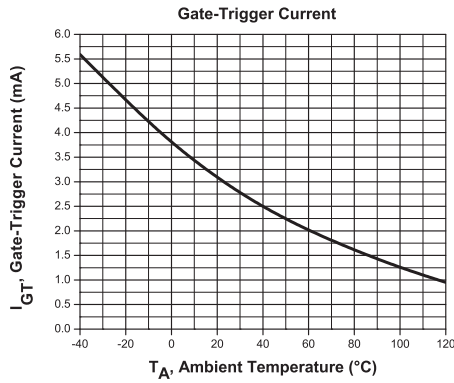
R4 (24-October 2013)

CS220-8B
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SILICON CONTROLLED RECTIFIERS
 8.0 AMP, 200 THRU 800 VOLT

TYPICAL ELECTRICAL CHARACTERISTICS



R4 (24-October 2013)